

FIG. 1A (PRIOR ART)

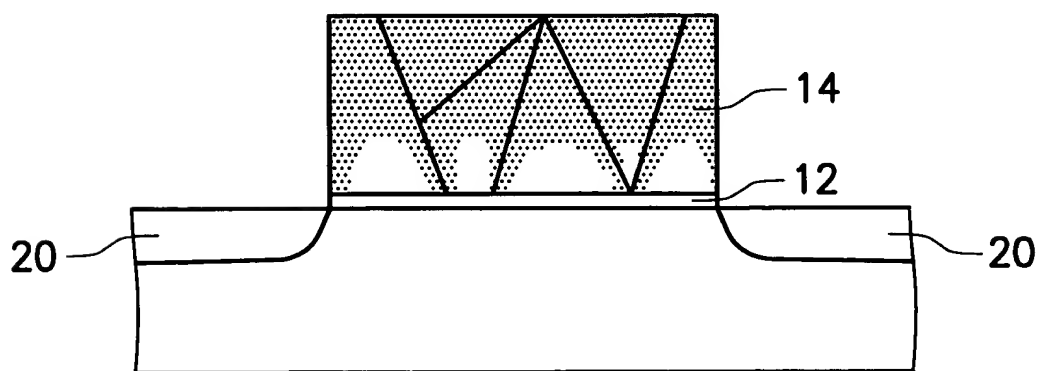


FIG. 1B (PRIOR ART)

A cross-sectional view of a semiconductor device. A substrate 20 is shown with a recessed region. A layer 12 is formed on the surface of the substrate 20. A patterned layer 14 is formed on top of layer 12, with a central rectangular region filled with a stippled pattern and two triangular regions on either side.

A cross-sectional view of a semiconductor device. A substrate 20 is shown with a thin layer 12 on its top surface. A patterned layer 14 is formed on top of layer 12, featuring a series of triangular shapes. The layer 14 is filled with a stippled pattern, and the triangular shapes are defined by solid lines.

FIG. 2 (PRIOR ART)

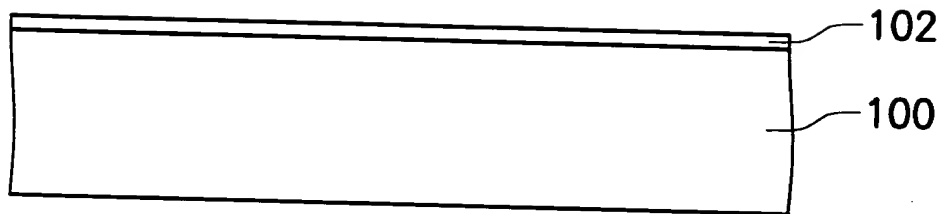


FIG. 3A

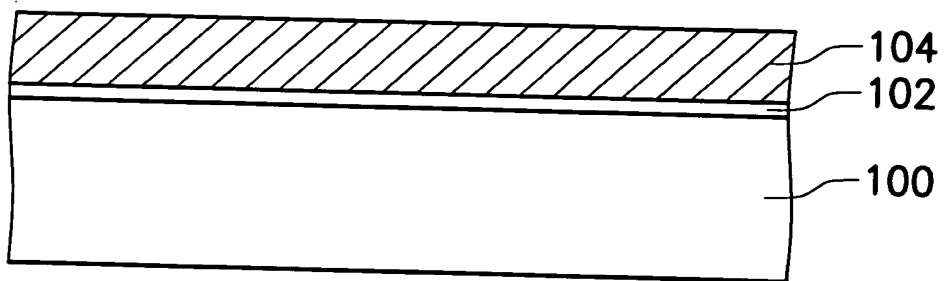


FIG. 3B

